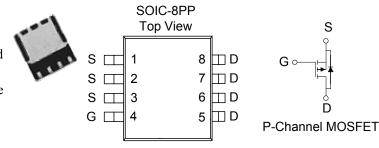
## **Analog Power**

## P-Channel 80-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8PP saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY				
<b>V</b> <sub>DS</sub> (V)	r <sub>DS(on)</sub> m(Ω)	$I_D(A)$		
-80	$75@V_{CS} = -10V$	-6.7		
-80	$90@V_{CS} = -4.5V$	-6.1		



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage		VDS	-80	V	
Cate-Source Voltage			±20	v	
	$T_A=25^{\circ}C$	T_	-6.7		
Continuous Drain Current <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	ID	-5.0	Α	
Pulsed Drain Current <sup>b</sup>			±50		
Continuous Source Current (Diode Conduction) <sup>a</sup>		Is	-2.1	Α	
	$T_A=25^{\circ}C$	PD	5.0	w	
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	гD	3.2	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
	t <= 10 sec	D	25	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	$R_{\theta JA}$	65	°C/W	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter	Sector	Test Conditions	Limits			Unit
Falanetei	Synton	Symbol Test Conditions		Тур	Max	
Static	· · ·					
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 V$ , $I_D = -250 \text{ uA}$	-30			
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \text{ uA}$	-1			ľ
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{CS} = \pm 20 V$			±100	nA
Zero Gate Voltage Drain Ourrent	l	$V_{DS} = -64 V, V_{GS} = 0 V$			-1	υA
	IDSS	$V_{DS}$ = -64 V, $V_{CS}$ = 0 V, $T_J$ = 55°C			-5	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS}$ = -5 V, $V_{GS}$ = -10 V	-50			Α
Drain-Source On-Resistance <sup>A</sup>	r	$V_{GS}$ = -10 V, I <sub>D</sub> = -6.7 A			75	mΩ
	r <sub>DS(on)</sub>	$V_{GS}$ = -4.5 V, I <sub>D</sub> = -6.1 A			90	
Forward Tranconductance <sup>A</sup>	9 <sub>fs</sub>	$V_{DS}$ = -15 V, $I_{D}$ = -6.7 A		29		S
Diode Forward Voltage	V <sub>SD</sub>	$I_{\rm S}$ = 2.5 A, $V_{\rm GS}$ = 0 V		-0.8		V
Dynamic <sup>b</sup>						
Total Gate Charge	Qg	$V_{DS} = -15 V, V_{GS} = -5 V,$		25		
Gate-Source Charge	Q <sub>gs</sub>	$v_{DS} = -15 v, v_{CS} = -5 v,$ $I_{D} = -6.7 A$		11		nC
Gate-Drain Charge	Q <sub>gd</sub>	I <sub>D</sub> = -0.7 A		17		
Tum-On Delay Time	t <sub>d(on)</sub>			15		
Rise Time	t <sub>r</sub>	$V_{DD}$ = -15 V, R <sub>L</sub> = 6 $\Omega$ ,		13		nS
Tum-Off Delay Time	t <sub>d(off)</sub>	ID=-1 A, VGEN=-10 V		100		
Fall-Time	t <sub>f</sub>			54		1

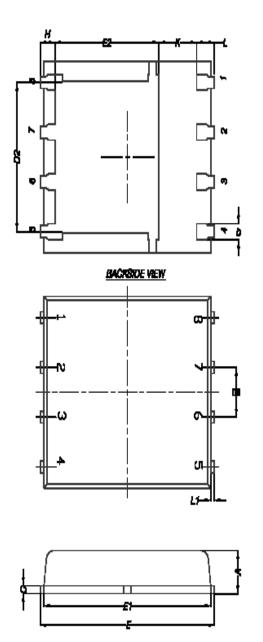
Notes

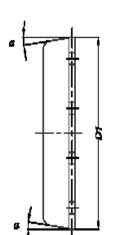
a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .

b. Guaranteed by design, not subject to production testing.

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## Package Information





	MRLLIMETERS			
DM.	KON.	NOM	KAX.	
•	38	1.00	1.10	
4	0.33	0.41	0.61	
0	0.20	0.25	ŝ	
D1	430	4.90	5.00	
D2	381	3.81	298	
Ε	5.90	6.00	8.10	
Ef	5.70	6.75	5.80	
22	8.96	3.58	278	
0	1.27 88C			
H	0.41	0.61	0.81	
ĸ	1.10	•	•	
L	0.61	0.67	0.71	
11	0.06	0.13	0.20	
Œ	¢	-	12*	